

# **Device Modeling Report**

COMPONENTS : VOLTAGE COMPARATOR  
PART NUMBER : LM319M  
MANUFACTURER : NATIONAL



**Bee Technologies Inc.**

## **BJT MODEL**

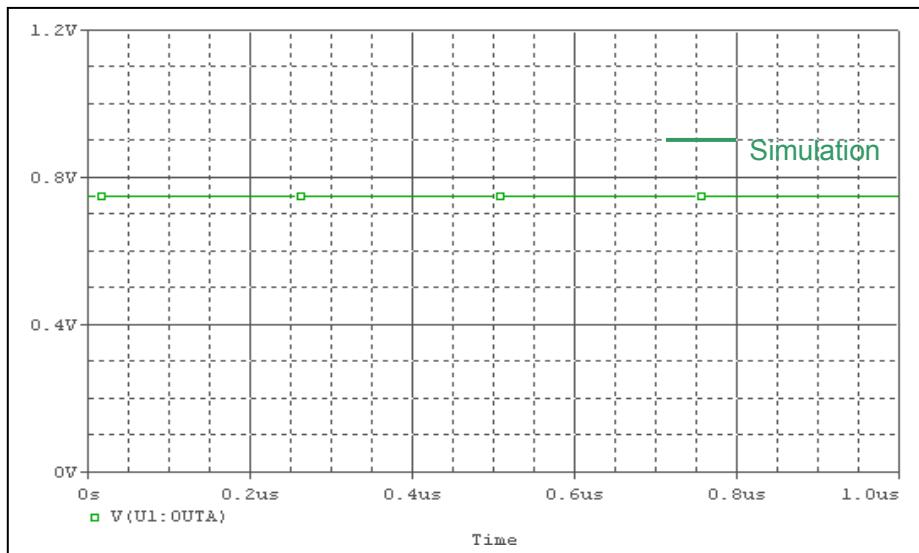
Pspice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
CJC	Zero-bias Collector-Base Junction Capacitance
TF	Forward Transit Time
TR	Reverse Transit Time

## **DIODE MODEL**

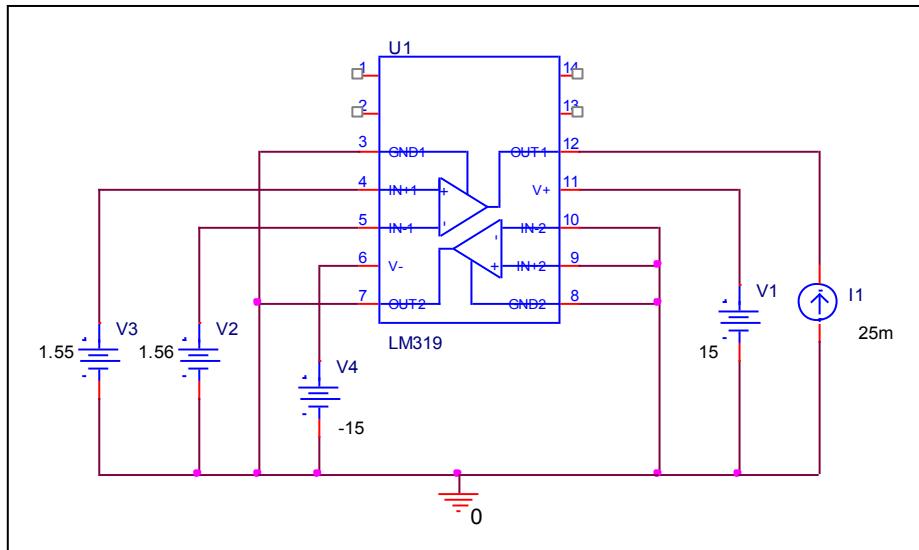
Pspice model parameter	Model description
IS	Saturation Current
RS	Series Resistance

## Output Low Voltage

Simulation result



Evaluation Circuit

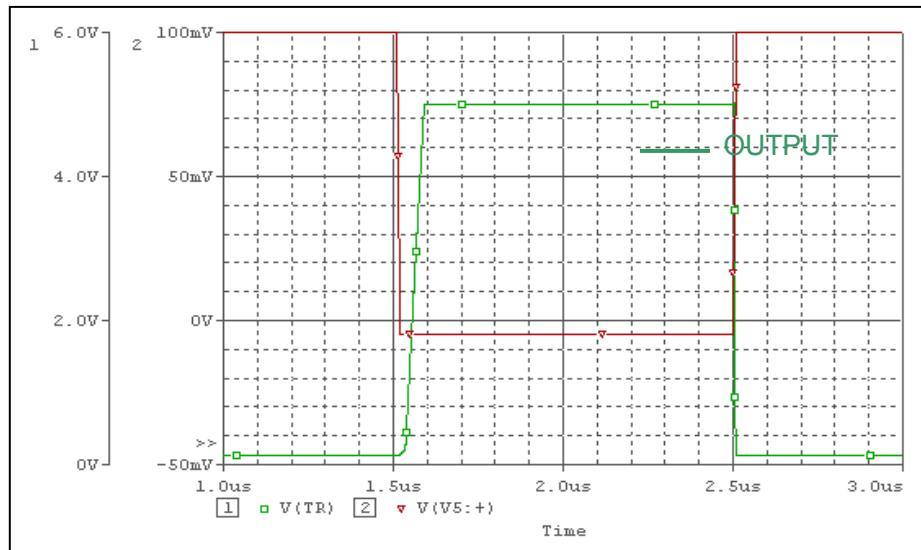


Comparison Table

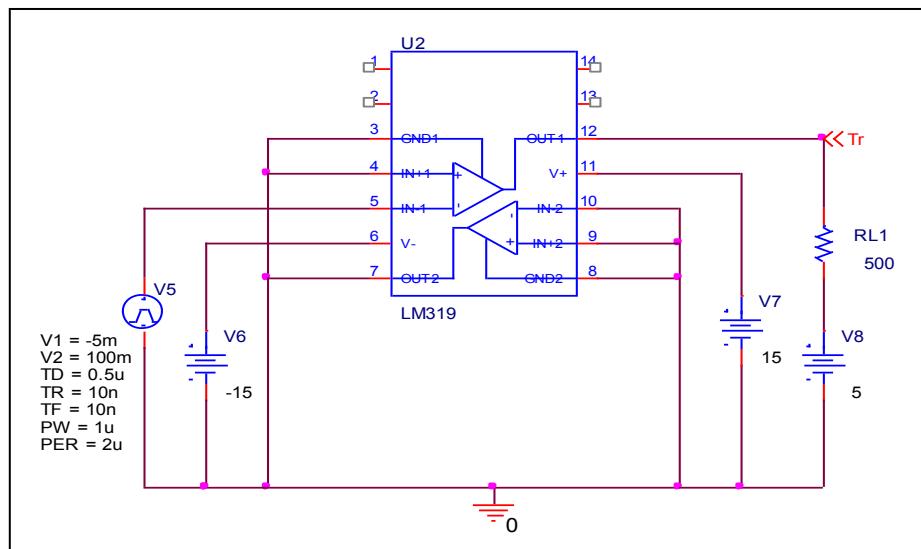
$I_o = 25\text{mA}$	Measurement	Simulation	%Error
$V_{ol} (\text{V})$	0.75	0.750451	0.06

## Response time (Rise time and Transition time)

### Simulation result



### Evaluation Circuit

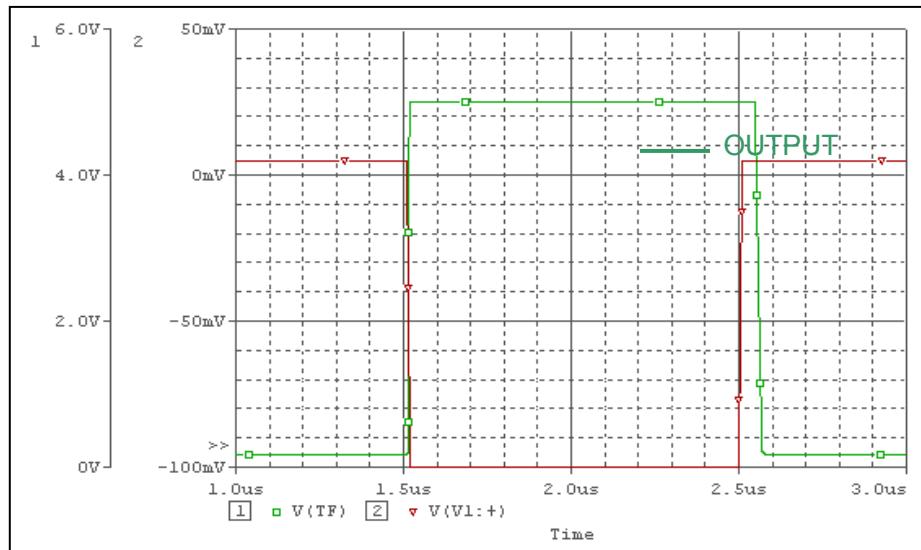


### Comparison Table

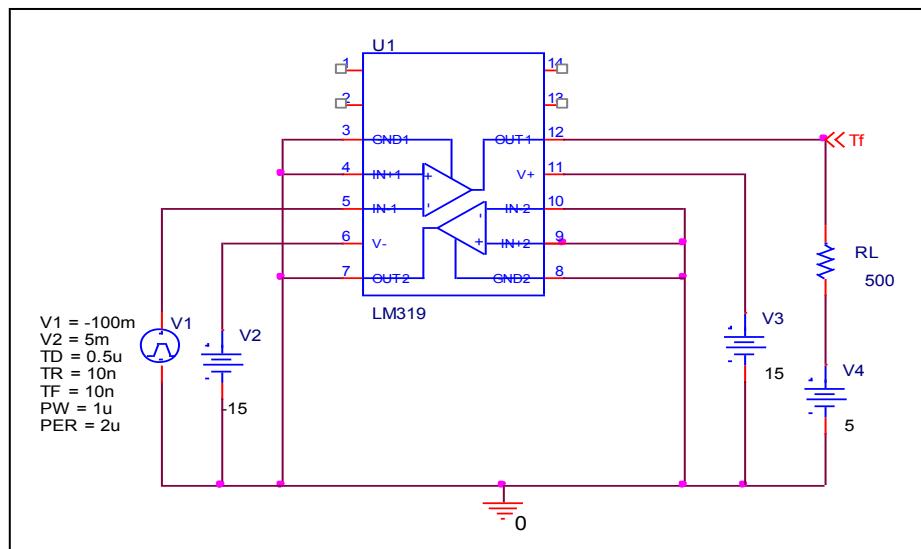
	Measurement	Simulation	% Error
Rising delay time (ns)	30	29.718	-0.940
Transition time (ns)	45	44.305	-1.544

## Response time (Falling time)

Simulation result



Evaluation Circuit

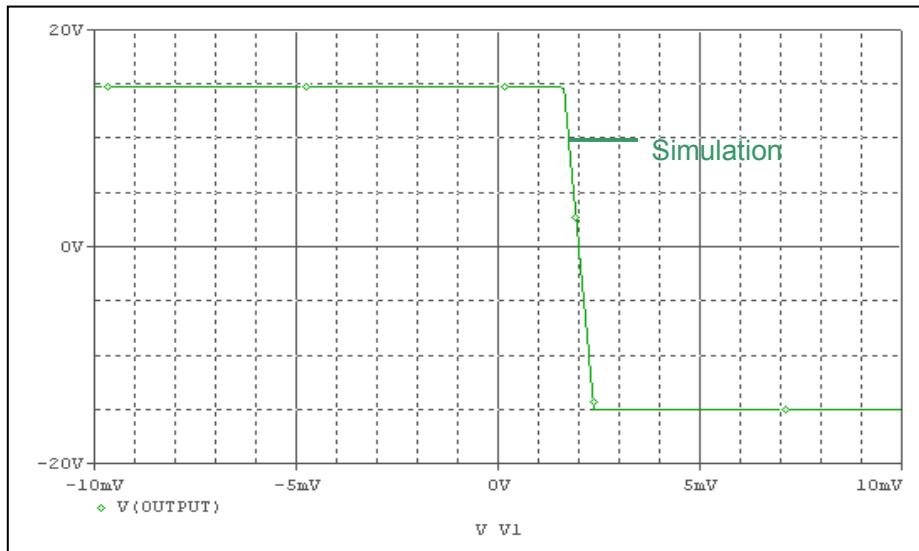


Comparison Table

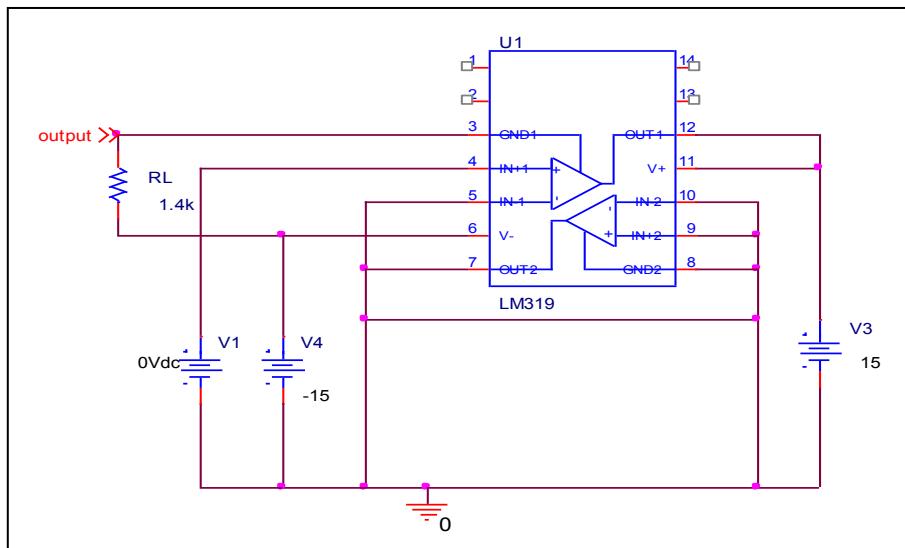
	Measurement	Simulation	% Error
Falling delay time (ns)	50	49.947	-0.106

## Input Offset Voltage Characteristics

Simulation result



Evaluation Circuit

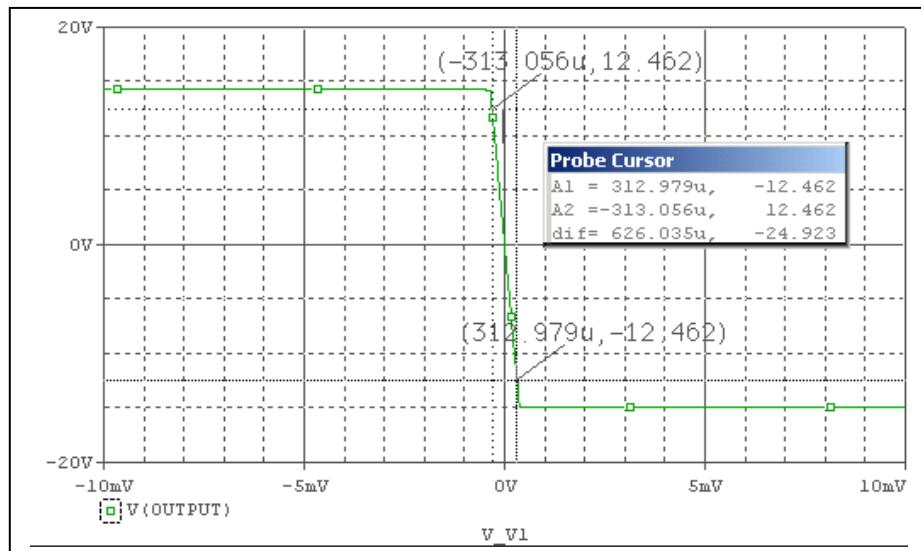


Comparison Table

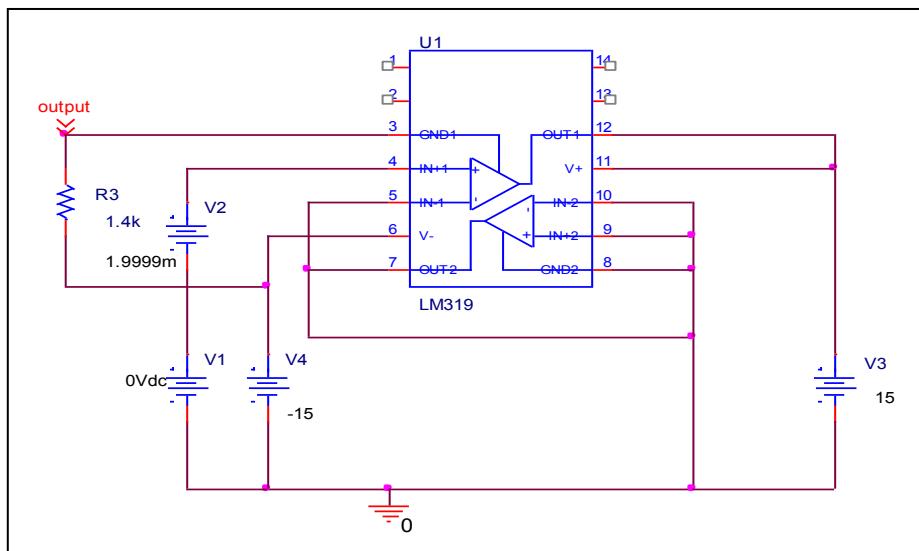
	Measurement	Simulation	%Error
$V_{io}$ (mV)	2	1.9999	-0.005

## Av Characteristics

### Simulation result



### Evaluation Circuit



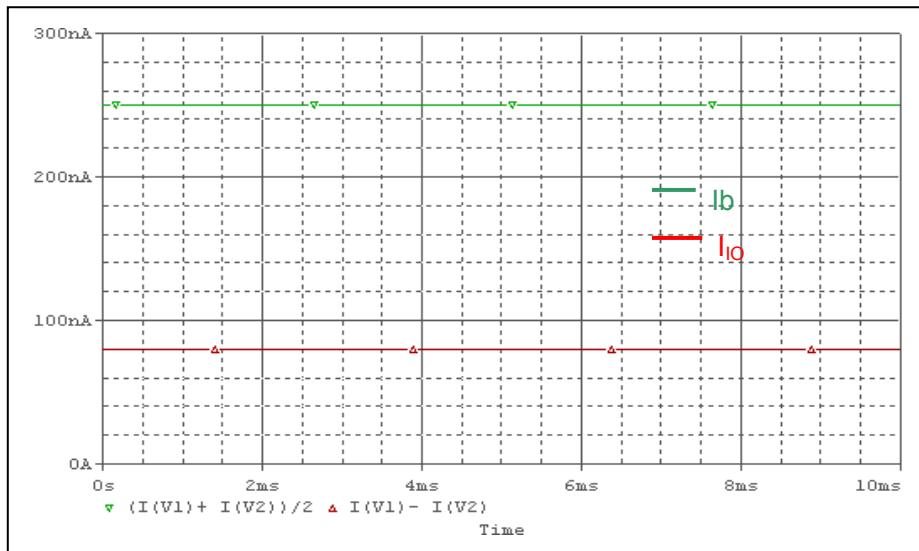
$$Av = 24.923 / 626.035u$$

### Comparison Table

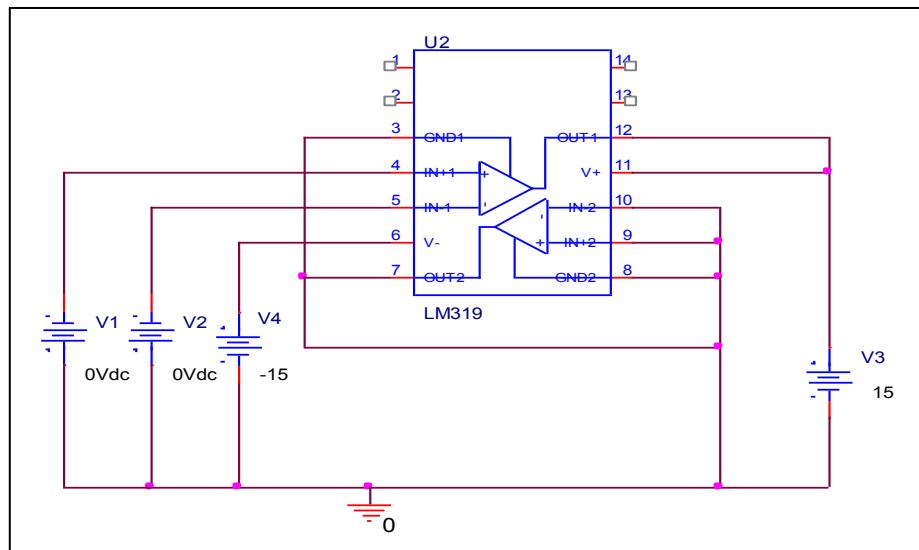
	<b>Measurement</b>	<b>Simulation</b>	<b>%Error</b>
<b>Av (V/mV)</b>	40	39.810	-0.475

## Input Bias Current Characteristics

Simulation result



Evaluation Circuit



Comparison Table

	Measurement	Simulation	% Error
$I_b$ (nA)	250	250.020	0.008
$I_o$ (nA)	80	79.988	-0.015